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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/753,662	01/04/2001	Shigeto Fujimura	1592-0131P	1881
7	590 • 03/28/2002			
BIRCH, STEWART, KOLASCH AND BIRCH, LLP			EXAMINER	
P.O. Box 747 Falls Church, VA 22040-0747		ANDERSON, MATTHEW A		
			ART UNIT	PAPER NUMBER

1765 DATE MAILED: 03/28/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

PTO-90C (Rev. 07-01)

Pr 182						
	Application No.	Applicant(s)				
Office Action Summary	09/753,662	FUJIMURA ET AL.				
omec Adden Gammary	Examiner	Art Unit				
The MAILING DATE of this communication con	Matthew A. Anderson	1765				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status						
1)⊠ Responsive to communication(s) filed on <u>04 J</u>	anuary 2001 .					
2a)☐ This action is FINAL . 2b)⊠ Thi	☐ This action is FINAL . 2b)☑ This action is non-final.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
4) Claim(s) <u>1</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers						
9)☐ The specification is objected to by the Examiner.						
10)⊠ The drawing(s) filed on <u>04 January 2001</u> is/are: a)⊠ accepted or b)⊡ objected to by the Examiner.						
Applicant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).				
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.						
If approved, corrected drawings are required in reply to this Office action.						
12)☐ The oath or declaration is objected to by the Examiner.						
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a)⊠ All b)□ Some * c)□ None of:						
1.⊠ Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
a) The translation of the foreign language provisional application has been received.						
15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachment(s)						
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal P	(PTO-413) Paper No(s) atent Application (PTO-152)				

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DETAILED ACTION

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Fukuda et al. (US 5,554,219).

Fukuda et al. discloses a process for the production of bulk single crystal ZnSe (zinc selenide). ZnSe is disclosed in the first sentence of col. 1 as a known semiconductor used in, for example, lasers. Having two components (zinc and selenium), ZnSe is also inherently a compound semiconductor. In col. 2 lines 18-29 and 44-57 is delineated a process which requires no pre-made seed crystal. This is the growth on the solid poly-crystal alternative to using a seed crystal. Example 3 in col. 3 uses this process. A VF (vertical Bridgeman as in the claims) or a VGF (vertical gradient freezing) furnace was used. A crucible was used to contain the melt formed from semiconductor raw material within the vertical furnace. The raw material was melted (i.e. heated with a heater) and then a portion at the lower tip of the crucible was solidified by cooling. The crystal growth was then stopped. Then part of the resultant poly-crystalline ZnSe in the crucible tip was re-melted. From the lower surface of the melt in contact with the remaining solid raw material, crystallization was resumed by cooling the

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melt by moving the crucible down at a certain (i.e. gradual) rate as disclosed in col. 3 lines 55+. The result, after solidification (col. 3 lines 60-63), was twin-free bulk single crystal ZnSe (col. 4 lines 2-3).

The examiner notes that nuclei are inherently the art accepted points at which crystal growth is initiated. Since Fukuda et al. discloses crystal growth from the surface of the polycrystalline formed from the melt, nucleation must have been inherently promoted at that surface. The examiner makes this argument fully cognizant of the art accepted 'nucleation—growth' hypothesis forwarded by the text book Kingery et al., <u>Introduction to Ceramics</u>, 2nd Ed., John Wiley and Sons, New York, NY, pp. 328-336, 1976.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew A. Anderson whose telephone number is (703) 308-0086. The examiner can normally be reached on M-Th, 6:30-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Benjamin Utech can be reached on (703) 308-3836. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9310 for regular communications and (703) 872-9311 for After Final communications.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0661.

MAA March 26, 2002

> BENJAMIN L. UTECH SUPERVISORY PATENT EXAMINER TECHNOLOGY GEN 4700

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